Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a TO220 package intended for use in applications requiring good bidirectional blocking voltage and high surge current capability and high junction temperature capability ($T_{i(max)} = 150$ °C).

2. Features and benefits

- High junction operating temperature capability (T_{i(max)} = 150 °C)
- High bidirectional blocking voltage capability
- · Very high current surge capability
- · High thermal cycling performance
- · Planar passivated for voltage ruggedness and reliability

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 136 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	20	Α
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; Fig. 4; Fig. 5	-	-	225	А
		half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$	-	-	248	Α
T _j	junction temperature		-	-	150	°C
Static ch	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$	5	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	40	mA
V _T	on-state voltage	I _T = 20 A; T _j = 25 °C; <u>Fig. 10</u>	-	-	1.6	V
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	400	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	. 51
2	А	anode		A K G
3	G	gate		sym037
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
TYN20-600TF	TO220	TYN20-600TFQ	Tube	50	SOT78	13-Jun-2008

7. Marking

Table 4. Marking codes

Type number	Marking codes
TYN20-600TF	TYN20
	600TF

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
V_{RRM}	repetitive peak reverse voltage		-	600	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 136 °C;	-	12.7	Α
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \le 136 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	20	А
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	225	А
		half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$	-	248	Α
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	254	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 20 mA	-	125	A/µs
I _{GM}	peak gate current		-	4	Α
V_{GM}	peak gate voltage		-	5	V
P_{GM}	peak gate power		-	10	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
T _i	junction temperature		-	150	°C

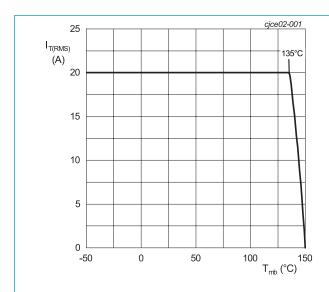
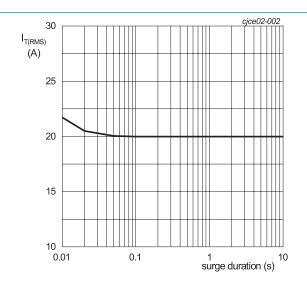
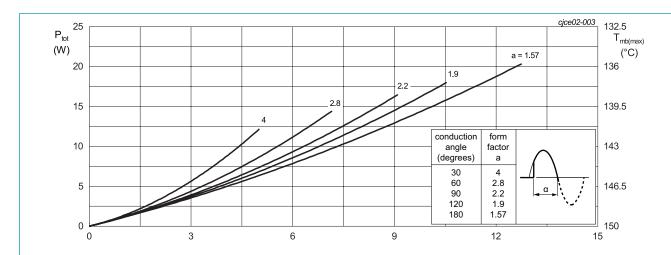


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; T_{mb} = 136 °C Fig. 2. RMS on-state current as a function of surge duration; maximum values

SCF



 α = conduction angle

a = form factor = $I_{T(RMS)}/I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

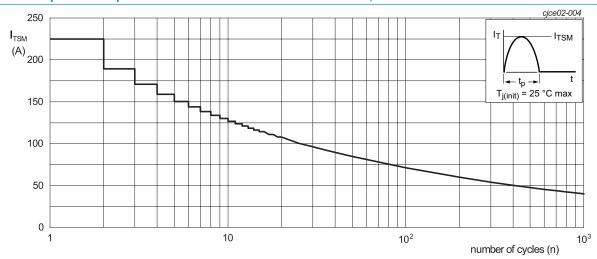
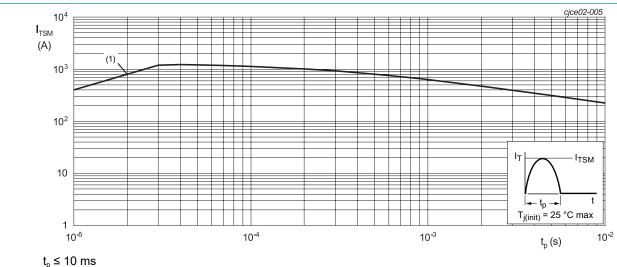


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



(1) dl_⊤/dt limit

f = 50 Hz

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 6	-	-	0.7	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

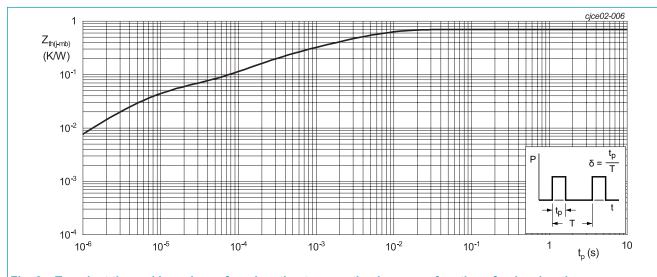


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$	5	-	10	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$	-	-	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	40	mA
V _T	on-state voltage	I _T = 20 A; T _j = 25 °C; <u>Fig. 10</u>	-	-	1.6	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 11</u>	-	8.0	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C	0.25	0.45	-	V
V_{GR}	gate reverse voltage	I _{RG} = 100 mA	10	-	-	V
I _D	off-state current	V _D = 600 V; T _j = 25 °C	-	-	10	μA
		V _D = 600 V; T _j = 150 °C	-	-	2	mA
I _R	reverse current	V _D = 600 V; T _j = 25 °C	-	-	10	μA
		V _D = 600 V; T _j = 150 °C	-	-	2	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	400	-	-	V/µs
\mathbf{t}_{gt}	gate-controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = 600 \text{ V}; I_G = 20 \text{ mA};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	2	-	μs
t _q	commutated turn-off time	I_{TM} = 2 A; t_p = 50 µs; dV/dt = 5 V/µs; dI/dt = 30 A/µs	-	-	12	μs

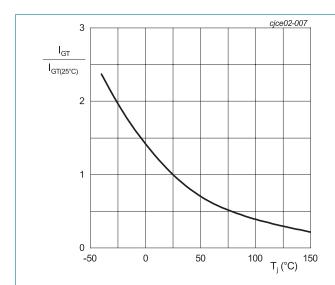


Fig. 7. Normalized gate trigger current as a function of junction temperature

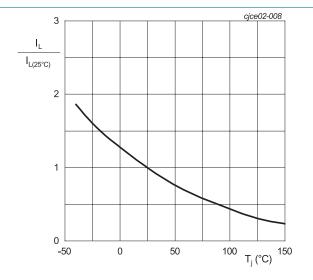


Fig. 8. Normalized latching current as a function of junction temperature

SCR

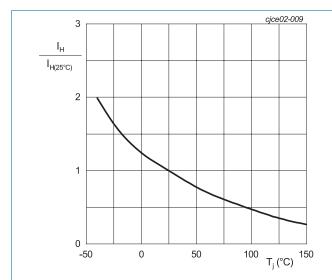
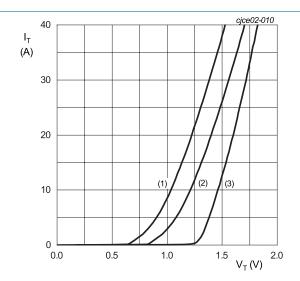


Fig. 9. Normalized holding current as a function of junction temperature



 $\begin{array}{l} V_o=1.058~V;~R_s=0.0171~\Omega\\ (1)~T_j=150~^{\circ}C;~typical~values\\ (2)~T_j=150~^{\circ}C;~maximum~values\\ (3)~T_j=25~^{\circ}C;~maximum~values \end{array}$

Fig. 10. On-state current as a function of on-state voltage

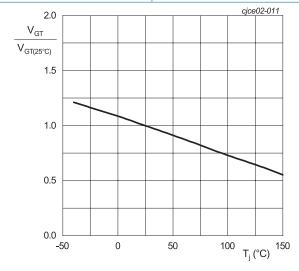
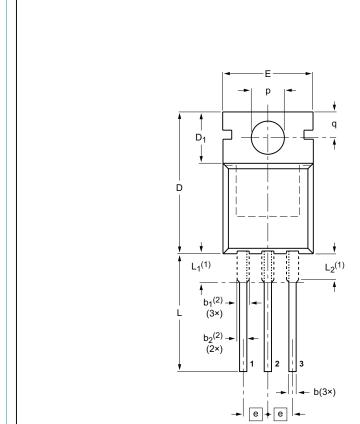


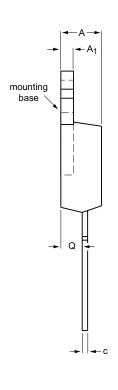
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

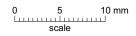
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11. Package outline



Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB





DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- Lead shoulder designs may vary.
 Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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